

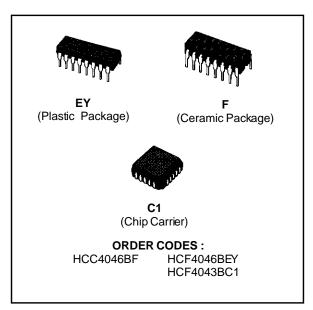
# HCC/HCF4046B

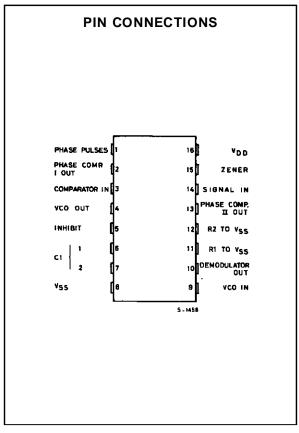
## MICROPOWER PHASE-LOCKED LOOP

- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- VERY LOW POWER CONSUMPTION : 100µW (TYP.) AT VCO f<sub>0</sub> = 10kHz, V<sub>DD</sub> = 5V
- OPERATING FREQUENCY RANGE : UP TO 1.4MHz (TYP.) AT V<sub>DD</sub> = 10V
- LOW FREQUENCY DRIFT : 0.06%/°C (typ.) AT V<sub>DD</sub> = 10V
- CHOICE OF TWO PHASE COMPARATORS:
   1) EXCLUSIVE OR NETWORK
   2) EDGE-CONTROLLED MEMORY NETWORK
   WITH PHASE-PULSE OUTPUT FOR LOCK INDICATION
- HIGH VCO LINEARITY: 1% (TYP.)
- VCO INHIBIT CONTROL FOR ON-OFF KE-YING AND ULTRA-LOW STANDBY POWER CONSUMPTION
- SOURCE-FOLLOWER OUTPUT OF VCO CONTROL INPUT (demod. output)
- ZENER DIODE TO ASSIST SUPPLY REGULA-TION
- 5V, 10V AND 15V PARAMETRIC RATING
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

### **DESCRIPTION**

The HCC4046B (extended temperature range) and HCF4046B (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package. The HCC/HCF4046B COS/MOS Micropower Phase-Locked Loop (PLL) consists of a low-power, linear voltage-controlled oscillator (VCO) and two different phase comparators having a common signal-input amplifier and a common comparator input. A 5.2V zener diode is provided for supply regulation if necessary.





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#### VCO Section

one or two external resistors (R1 or R1 and R2). Resistor R1 and capacitor C1 determine the frequency range of the VCO and resistor R2 enables the VCO to have a frequency offset if required. The high input impedance ( $10^{12\Omega}$ ) of the VCO simplifiers the design of low-pass filters by permitting the designer a wide choice of resistor-to-capacitor ratios. In order not to load the low-pass filter, a source-follower output of the VCO input voltage is provided at terminal 10 (DE-MODULATED OUTPUT). If this terminal is used, a load resistor (Rs) of 10 k $\Omega$  or more should be connected from this terminal to Vss. If unused this terminal should be left open. The VCO can be connected either directly or through frequency dividers to the comparator input of the phase comparators. A full COS/MOS logic swing is available at the output of the VCO and allows direct coupling to COS/MOS frequency dividers such as the HCC/HCF4024B, HCC/HCF4018B, HCC/HCF4020B, HCC/HCF4022B. HCC/HCF4029B.and HBC/HBF4059A. One or more HCC/HCF4018B (Presettable Divide-by-N Counter) or HCC/HCF4029B (Presettable Up/Down Counter), or HBC/HBF4059A (Programmable Divide-by-"N" Counter), together with the HCC/HCF4046B (Phase-Locked Loop) can be used to build a micropower low-frequency synthe sizer. A logic 0 on the INHIBIT input "enables" the VCO and the source follower, while a logic 1 "turns off" both to minimize stand-by power consumption.

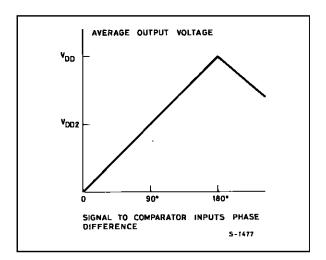
The VCO requires one external capacitor C1 and

### **Phase Comparators**

The phase-comparator signal input (terminal 14) can be direct-coupled provided the signal swing is within COS/MOS logic levels [logic "0" ≤ 30 %  $(V_{DD} - V_{SS})$ , logic "1"  $\geq 70 \% (V_{DD} - V_{SS})$ ]. For smaller swings the signal must be capacitively coupled to the self-biasing amplifier at the signal input. Phase comparator I is an exclusive-OR network; it operates analogously to an over-driven balanced mixer. To maximize the lock range, the signal-and comparator-input frequencies must have a 50% duty cycle. With no signal or noise on the signal input, this phase comparator has an average output voltage equal to V<sub>DD</sub>/2. The low-pass filter connected to the output of phase comparator I supplies the averaged voltage to the VCO input, and causes the VCO to oscillate at the center frequency (f<sub>o</sub>). The frequency range of input signals on which the PLL will lock if it was initially out of lock is defined as the frequency capture range (2 fc). The frequency range of input signals on which the loop will stay locked if it was initially in lock is defined as the frequency lock range (2  $f_L$ ). The capture range is  $\leq$  the lock range. With phase comparator I the range of frequencies over which the PLL can acquire lock (capture range) is dependent on the low-pass-filter characteristics, and can be made as large as the lock range. Phase-comparator I enables a PLL system to remain in lock in spite of high amounts of noise in the input signal. One characteristic of this type of phase comparator is that it may lock onto input frequencies that are close to harmonics of the VCO center-frequency. A second characteristic is that the phase angle between the signal and the comparator input varies between 0° and 180°, and is 90° at the center frequency. Fig. (a) shows the typical, triangular, phase-to-output response characteristic of phase-comparator I. Typical waveforms for a COS/MOS phase-locked-loop employing phase comparator I in locked condition of fo is shown in fig. (b). Phase-comparator II is an edge-controlled digital memory network. It consists of four flip-flop stages, control gating, and a three-stage output-circuit comprising p- and n-type drivers having a common output node. When the p-MOS or n-MOS drivers are ON they pull the output up to V<sub>DD</sub> or down to V<sub>SS</sub>, respectively. This type of phase comparator acts only on the positive edges of the signal and comparator inputs. The duty cycles of the signal and comparator inputs are not important since positive transitions control the PLL system utilizing this type of comparator. If the signal-input frequency is higher than the comparator-input frequency, the p-type output driver is maintained ON most of the time, and both the n- and p-drivers OFF (3 state) the remainder of the time. If the signal-input frequency is lower than the comparator-input frequency, the n-type output driver is maintained ON most of the time, and both the n- and p-drivers OFF (3 state) the remainder of the time. If the signal and comparator-input frequencies are the same, but the signal input lags the comparator input in phase, the n-type output driver is maintained ON for a time corresponding to the phase difference. If the signal and comparatorinput frequencies are the same, but the comparator input lags the signal in phase, the p-type output driver is maintained ON for a time corresponding to the phase difference. Subsequently, the capacitor voltage of the low-pass filter connected to this phase comparator is adjusted until the signal and comparator inputs are equal in both phase and frequency. At this stable point both p- and n-type output drivers remain OFF and thus the phase comparator output becomes an open circuit and holds the voltage on the capacitor of the low-pass filter constant. Moreover the signal at the "phase pulses" output is a high level which can be used for indicating a locked condition. Thus, for phase comparator II, no phase difference exists between signal and comparator

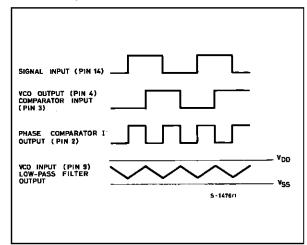
input over the full VCO frequency range. Moreover, the power dissipation due to the low-pass filter is reduced when this type of phase comparator is used because both the p- and n-type output drivers are OFF for most of the signal input cycle. It should be noted that the PLL lock range for this type of phase

Figure a : Phase-Comparator I Characteristics at Low-Pass Filter Output.

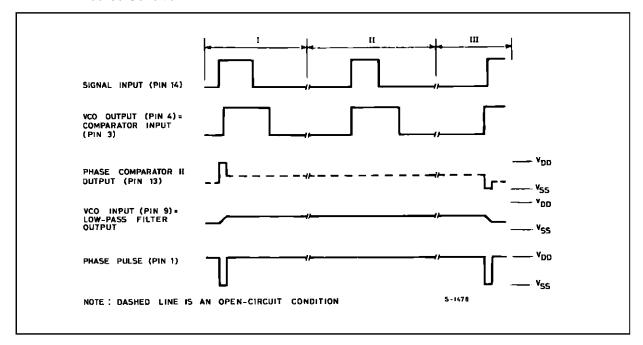


comparator is equal to the capture range, independent of the low-pass filter. With no signal present at the signal input, the VCO is adjusted to its lowest frequency for phase comparator II. Fig. (c) shows typical waveforms for a COS/MOS PLL employing phase comparator II in a locked condition.

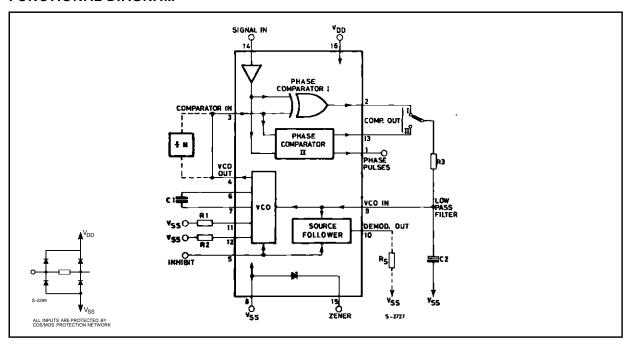
Figure b: Typical Waveforms for COS/MOS Phase Locked-Loop Employing Phase Comparator I in Locked Condition of fo.



**Figure C**: Typical Waveforms For COS/MOS Phase-locked Loop Employing Phase Comparator II In Locked Condition.



### **FUNCTIONAL DIAGRAM**



## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage : <b>HCC</b> Types <b>HCF</b> Types	- 0.5 to + 20 - 0.5 to + 18	V
Vi	Input Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
$I_1$	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package-temperature Range	200 100	mW mW
Тор	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	℃
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	∞

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

\* All voltage values are referred to V<sub>SS</sub> pin voltage.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
VI	Input Voltage	0 to V <sub>DD</sub>	V
Top	Operating Temperature : <b>HCC</b> Types <b>HCF</b> Types	- 55 to + 125 - 40 to + 85	°C



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Т	est Con	dition	S				Value				
Symbol	Parame	ter	٧ı	٧o	I <sub>0</sub>	V <sub>DD</sub>	T <sub>L</sub> ,	o w*		25°C		T <sub>Hi</sub>	gh*	Unit
,			(V)	(V)	(μA)	(V)	Min.	Max.	Min.		Max.	Min.	Max.	
vco s	ECTION													
V <sub>OH</sub>	Output High	1	0/ 5		< 1	5	4.95		4.95	5		4.95		
	Voltage		0/10		< 1	10	9.95		9.95	10		9.95		
	_		0/15		< 1	15	14.95		14.95	15		14.95		
$V_{OL}$	Output Low		5/0		< 1	5		0.05			0.05		0.05	V
	Voltage		10/0		< 1	10		0.05			0.05		0.05	
			15/0		< 1	15		0.05			0.05		0.05	
I <sub>OH</sub>	Output		0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		
	Drive	HCC	0/ 5	4.6		5	- 0.64		- 0.51			- 0.36		
	Current	Types	_	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
			0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
		HCF	0/ 5	4.6		5	- 0.52		- 0.44			- 0.36		
		Types	0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		mΑ
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
$I_{OL}$	Output	HCC	0/ 5	0.4		5	0.64		0.51	1		0.36		
	Sink	Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current		0/15	1.5		15	4.2		3.4	6.8		2.4		
			0/ 5	0.4		5	0.52		0.44	1		0.36		
		Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		Турез	0/15	1.5		15	3.6		3.0	6.8		2.4		
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage	HCC Types	0/18	Any In	nut.	18		± 0.1		± 10 <sup>-5</sup>	± 0.1		± 1	μΑ
	Current	HCF Types	0/15	Ally III	iput	15		± 0.3		± 10 <sup>-5</sup>	± 0.3		± 1	μΑ
PHASE	COMPARA		ECTIO	ON										
I <sub>DD</sub>	Total Device		0/ 5			5		0.1		0.05	0.1		0.1	
22	Current		0/10			10		0.5		0.25	0.5		0.5	A
	Pin 14 = Ope		0/15			15		1.5		0.75	1.5		1.5	mA
	Pin $5 = V_{DD}$		0/20			20		4		2	4		4	
	Pin 14 = V <sub>SS</sub>		0/ 5			5		5		0.04	5		150	
	or V <sub>DD</sub>	HCC	0/10			10		10		0.04	10		300	
	Pin $5 = V_{DD}$	Types	0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	μΑ
		HCF	0/ 5			5		20		0.04	20		150	
		Types	0/10			10		40		0.04	40		300	
		Types	0/15			15		80		0.04	80		600	
I <sub>OH</sub>	Output		0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		
	Drive	HCC	0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
	Current	Types	0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		mΔ
			0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		mA
		HCF	0/ 5	4.6		5	- 0.52		- 0.44			- 0.36		
		Types	0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		



<sup>\*</sup>  $T_{Low} = -55^{\circ}\text{C}$  for HCC device:  $-40^{\circ}\text{C}$  for HCF device. \*  $T_{High} = +125^{\circ}\text{C}$  for HCC device:  $+85^{\circ}\text{C}$  for HCF device. The Noise Margin for both "1" and "0" level is: 1V min. with  $V_{DD} = 5V$ , 2V min. with  $V_{DD} = 10V$ , 2.5V min. with  $V_{DD} = 15V$ .

## STATIC ELECTRICAL CHARACTERISTICS (continued)

			Т	est Con	dition	s	Value							
Symbol	Symbol Parameter		٧ı	٧o	I <sub>0</sub>	V <sub>DD</sub>	ΤL	o w*		25°C		T <sub>H</sub> i	gh*	Unit
			(V)	(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
I <sub>OL</sub>	Output	нсс	0/ 5	0.4		5	0.64		0.51	1		0.36		
	Sink	Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current	Туроо	0/15	1.5		15	4.2		3.4	6.8		2.4		mA
		HCF	0/ 5	0.4		5	0.52		0.44	1		0.36		шА
		Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		1,7,000	0/15	1.5		15	3.6		3.0	6.8		2.4		
$V_{IH}$	Input High			0.5/4.5	< 1	5	3.5		3.5			3.5		
	Voltage			1/9	< 1	10	7		7			7		V
				1.5/13.5	< 1	15	11		11			11		
$V_{IL}$	Input Low			4.5/0.5	< 1	5		1.5			1.5		1.5	
	Voltage			9/1	< 1	10		3			3		3	V
				13.5/1.5	< 1	15		4			4		4	
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage Current	HCC Types	0/18	Any In	put	18		± 0.1		± 10 <sup>-5</sup>	± 0.1		± 1	μΑ
	(except. pin 14)	HCF Types	0/15	, <b>,</b>	<b>P</b> •••	15		± 0.3		± 10 <sup>-5</sup>	± 0.3		± 1	<b>F.</b> .
I <sub>OUT</sub>	3-state Leakage	HCC Types	0/18	0/18		18		± 0.4		± 10 <sup>-4</sup>	± 0.4		± 12	μА
	Current	HCF Types	0/15	0/15		15		± 1.0		± 10 <sup>-4</sup>	± 1.0		± 7.5	μι
$C_1$	Input Capa	citance		Any In	put					5	7.5			pF

<sup>\*</sup>  $T_{Low} = -55^{\circ}\text{C}$  for HCC device:  $-40^{\circ}\text{C}$  for HCF device. \*  $T_{High} = +125^{\circ}\text{C}$  for HCC device:  $+85^{\circ}\text{C}$  for HCF device. The Noise Margin for both "1" and "0" level is: 1V min. with  $V_{DD} = 5V$ , 2V min. with  $V_{DD} = 10V$ , 2.5V min. with  $V_{DD} = 15V$ .

# **ELECTRICAL CARACTERISTICS** (T<sub>amb</sub> = 25 °C)

Symbol	Parameter	Test Conditions			Value		Unit
Syllibol	raiailletei		$V_{DD}$ (V)	Min.	Min. Typ.		<u> </u>
VCO SE	CTION						
P <sub>D</sub>	Operating Power	fo = 10 KHz R1 = 10 M $\Omega$	5		70	140	
	Dissipation	$R2 = \infty \qquad V_{COIN} = \frac{V_{DD}}{2}$	10		800	1600	μW
		2	15		3000	6000	
f <sub>max</sub>	Maximum Frequency	R1 = $10 \text{ K}\Omega$ C1 = $50 \text{ pF}$	5	0.3	0.6		
	, ,	$R2 = \infty$ $V_{COIN} = V_{DD}$	10	0.6	1.2		
			15	0.8	1.6		MHz
		$R1 = 5 \text{ K}\Omega$ $n \text{ C1} = 50 \text{ pF}$	5	0.5	0.8		
		$R2 = \infty$ $V_{COIN} = V_{DD}$	10	1	1.4		
			15	1.4	2.4		
	Center Frequency (f <sub>0</sub> ) and Frequency Range f <sub>max</sub> - f <sub>min</sub>	Programmable with exteri	nal compone	nts R1,	R2 and 0	C1	
	Linearity	$V_{COIN}$ =2.5 $V^{\pm0.3}$ R1=10 K $\Omega$	5		1.7		
		$V_{COIN}=5V^{\pm 1}$ R1=100 K $\Omega$	10		0.5		
		$V_{COIN}$ =5 $V^{\pm 2.5}$ R1=400 KΩ	10		4		%
		$V_{COIN}$ =7.5 $V^{\pm 1.5}$ R1=100 KΩ	15		0.5		
		$V_{COIN}$ =7.5 $V^{\pm 5}$ R1=1 M $\Omega$	15		7		
	Temperature Frequency		5		±0.12		
	Stability (no frequency		10		±0.04		
	offset) $f_{min} = 0$		15		±0.015		%/°C
	Temperature Frequency		5		±0.09		
	Stability (frequency offset)		10		±0.07		
	f <sub>min</sub> ≠ 0		15		±0.03		
Vco	Output Duty Cycle		5, 10, 15		50		%
$t_{THL}$	VCO Output Transition		5		100	200	
tтьн	Time		10		50	100	ns
			15		40	80	
	Source Follower Output (demodulated Output): Offset Voltage V <sub>COIN</sub> - V <sub>DEM</sub>	R <sub>S</sub> > 10 KΩ	5, 10, 15		1.8	2.5	V
	Source Follower Output	R <sub>S</sub> =100 KΩ $V_{COIN}=2.5^{\pm0.3}V$	5		0.3		
	(demodulated Output):	R <sub>S</sub> =300 K $\Omega$ V <sub>COIN</sub> =5 <sup>±2.5</sup> V	10		0.7		%
	Linearity	Rs=500 K $\Omega$ Vcoin=7.5 $^{\pm 5}$ V	15		0.9		
$V_{Z}$	Zener Diode Voltage	$I_Z = 50 \mu A$		4.45	5.5	7.5	V
Rz	Zener Dynamic Resistance	$I_Z = 1 \text{ mA}$			40		Ω
PHASE	COMPARATOR SECTION						
R14	Pin 14 (signal in) Input		5	1	2		
	Resistance		10	0.2	0.4		МΩ
			15	0.1	0.2		
	A.C. Coupled Signal Input	f <sub>in</sub> = 100 KHz sine wave	5	180	360		
	Voltage Sensitivity *		10	330	660		mV
	(peak to paek)		15	900	1800		

## **ELECTRICAL CHARACTERISTICS** (continued)

Cumbel	Parameter	Test Conditions		Value			
Symbol	Parameter —	V <sub>DD</sub> (	√) Min.	Тур.	Max.	Unit	
PHASE	COMPARATOR SECTION (cont'd)	•	•	•			
T <sub>PHL</sub>	Propagation Delay Time High to	5	225	450			
	Low Level Pins 14 to 13	10	100	200		ns	
		15	65	130			
T <sub>PLH</sub>	Propagation Delay Time Low to	5		350	700		
	High, Level	10		150	300	ns	
		15		100	200		
T <sub>PHZ</sub>	Propagation Delay Time 3-state	5		225	450		
	High Level to High Impedance Pins 14 to 13	10		100	200	ns	
	PINS 14 to 13	15		65	130		
T <sub>PLZ</sub>	Low Level to High Impedance	5		285	570		
		10		130	260	ns	
		15		95	190		
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time	5			50		
	Comparator Pin 3	10			1	μs	
		15			0.3		
	Signal Pin 14	5			500		
		10			20	μs	
		15			2.5		
T <sub>THL</sub> ,	Transition Time	5		100	200		
$T_{TLH}$		10		50	100	ns	
		15		40	80		

 $<sup>^{\</sup>star}$  For sine wave the frequency must be greater than 10KHz for Phase Comparator II.

### **DESIGN INFORMATION**

This information is a guide for approximating the values of external components for the HCC/HCF 4046B in a Phase-Locked-Loop system. The selected external components must be within the following ranges :

 $5k\Omega \le R1$ , R2,  $R_S \le 1M\Omega$ 

 $C1 \ge 100 pF$  at  $V_{DD} \ge 5V$ 

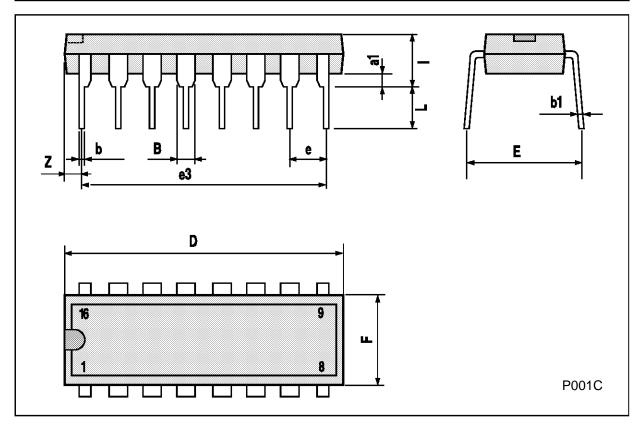
 $C1 \ge 50 pF$  at  $V_{DD} \ge 10 V$ 

	USING PHASE (	COMPARATOR I	USING PHASE (	COMPARATOR II		
CHARACTERISTICS	VCO WITHOUT OFFSET R2 = ∞	VCO WITH OFFSET	VCO WITHOUT OFFSET R2 = ∞	VCO WITH OFFSET		
VCO Frequency	fmax to VDD2 VDD VCO INPUT VOLTAGE S-1679	**************************************	to voo input voltage s-1679	Tmax  to Tmin  VD02 VD0 VCO INPUT VOLTAGE 5-1460		
For No Signal Input	VCO in PLL System w frequency f₀	rill Adjust to centre	VCO in PLL System v Operating Frequency			
Frequency Lock Range, 2 f <sub>L</sub>			frequency range <sub>nax</sub> - f <sub>min</sub>			
Frequency Capture Range, 2 f <sub>C</sub>	1N O R3 T1 = R3 C2 C2	00UT  (1),(2) $2f_{C} = \frac{1}{\pi} \sqrt{\frac{2\pi f_{L}}{\Upsilon 1}}$ 5-1483				
Loop Filter Component Selection	$f_{C} = f_{L}$ Selection $f_{C} = f_{L}$ $f_{C} = f_{L}$					
Phase Angle Between Signal and Comparator	90° at Centre Frequen 0° and 180° at ends o		Always 0° in lock			
Locks on Harmonics of Centre Frequency	Ye	es	No			
Signal Input Noise Rejection * G.S. Mosckytz "miniatur	High Low zed RC filters using phase Lockedloop" BSTJ, may 1965					

<sup>\*</sup> G.S. Mosckytz "miniaturized RC filters using phase Lockedloop" BSTJ, may 1965

# Plastic DIP16 (0.25) MECHANICAL DATA

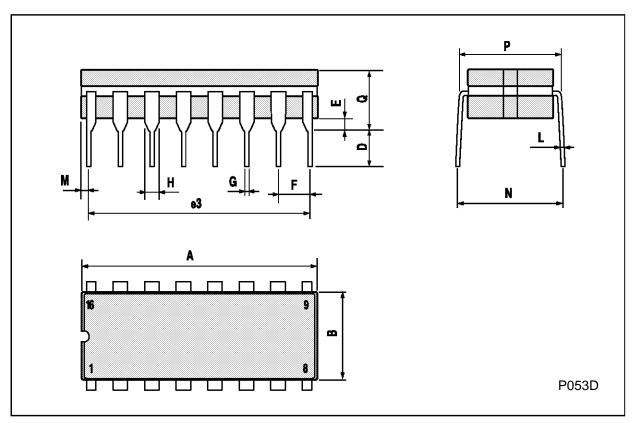
DIM.		mm			inch	
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



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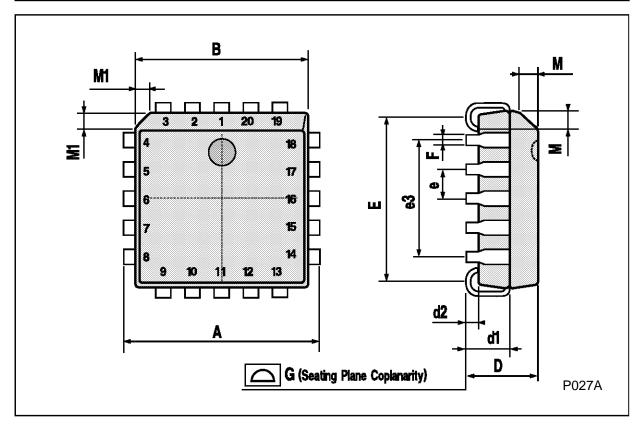
# **Ceramic DIP16/1 MECHANICAL DATA**

DIM.		mm			inch	
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			20			0.787
В			7			0.276
D		3.3			0.130	
Е	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
Н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
М	0.51		1.27	0.020		0.050
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



## **PLCC20 MECHANICAL DATA**

DIM.		mm		inch					
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
Α	9.78		10.03	0.385		0.395			
В	8.89		9.04	0.350		0.356			
D	4.2		4.57	0.165		0.180			
d1		2.54			0.100				
d2		0.56			0.022				
E	7.37		8.38	0.290		0.330			
е		1.27			0.050				
e3		5.08			0.200				
F		0.38			0.015				
G			0.101			0.004			
М		1.27			0.050				
M1		1.14			0.045				



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